



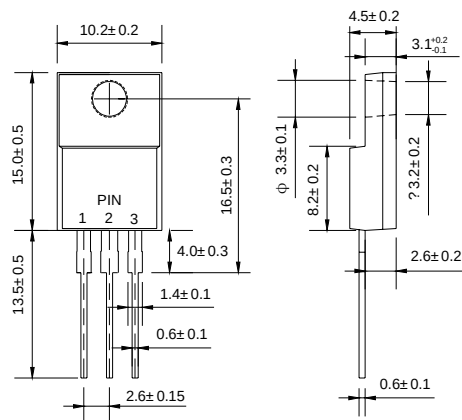
ITO-220AB

Features

- ◇ High surge capacity.
- ◇ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.
- ◇ Metal silicon junction, majority carrier conduction.
- ◇ High current capacity, low forward voltage drop.
- ◇ Guard ring for over voltage protection.

Mechanical Data

- ◇ Case: JEDEC ITO-220AB, molded plastic body
- ◇ Polarity: As marked
- ◇ Position: Any
- ◇ Weight: 0.06 ounce, 1.67 grams



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

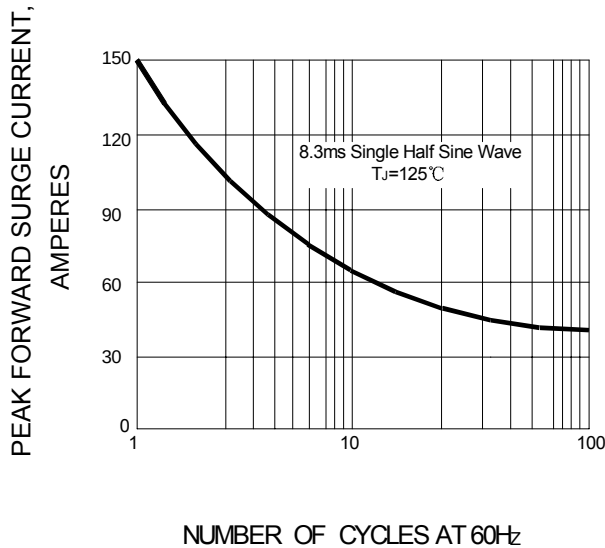
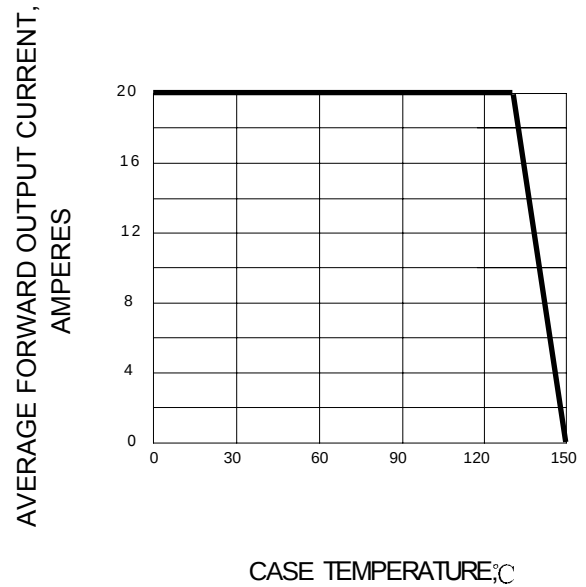
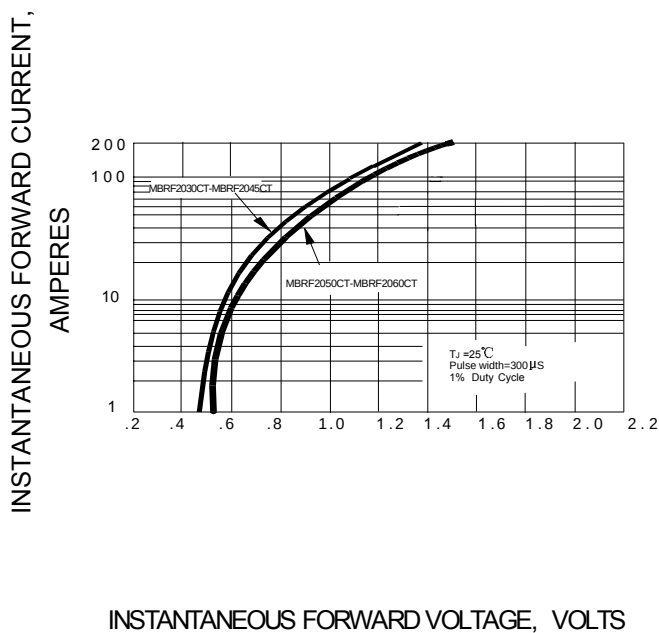
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

		MBR 2030FCT	MBR 2035FCT	MBR 2040FCT	MBR 2045FCT	MBR 2050FCT	MBR 2060FCT	UNITS
Maximum recurrent peak reverse voltage	V _{RRM}	30	35	40	45	50	60	V
Maximum RMS Voltage	V _{RMS}	21	25	28	32	35	42	V
Maximum DC blocking voltage	V _{DC}	30	35	40	45	50	60	V
Maximum average forward total device rectified current @T _C = 135°C	I _{F(AV)}	20						A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I _{FSM}	150						A
Maximum forward voltage (Note 1) (I _F =10A,T _C =25 °C) (I _F =10A,T _C =125 °C) (I _F =20A,T _C =25°C) (I _F =20A,T _C =125°C)	V _F	- 0.57 0.84 0.72				0.80 0.70 0.95 0.85		V
Maximum reverse current @T _C =25°C at rated DC blocking voltage @T _C =125°C	I _R	0.1 15				0.15 150		m A
Maximum thermal resistance (Note2)	R _{θJC}	2.0						°C/W
Operating junction temperature range	T _J	- 55 ---- + 150						°C
Storage temperature range	T _{STG}	- 55 ---- + 150						°C

NOTE: 1. Pulse test: 300μs pulse width, 1% duty cycle.

2. Thermal resistance from junction to case.

Ratings AND Characteristic Curves

FIG.1 – PEAK FORWARD SURGE CURRENT

FIG.2 – FORWARD DERATING CURVE

FIG.3 – TYPICAL FORWARD CHARACTERISTIC

FIG.4 – TYPICAL REVERSE CHARACTERISTIC
